

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

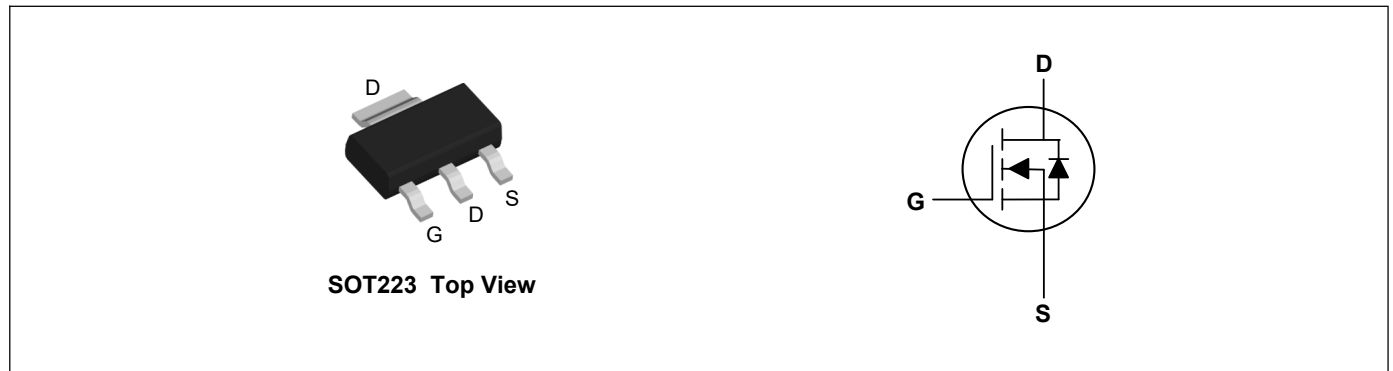
Product Summary



V_{DS}	100	V
I_D	2.2	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	310	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	320	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=25^{\circ}C$	2.2	A
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_A=70^{\circ}C$	1.7	A
Pulsed Drain Current ²	I_{DM}	5.5	A
Total Power Dissipation ³	$P_D@T_A=25^{\circ}C$	1.5	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	85	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	36	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =2A	---	260	310	mΩ
		V _{GS} =4.5V, I _D =1A	---	270	320	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =2A	---	2.4	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.8	---	Ω
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =2A	---	9.3	---	nC
Gate-Source Charge	Q _{gs}		---	2	---	
Gate-Drain Charge	Q _{gd}		---	1.5	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω, I _D =2A	---	2	---	ns
Rise Time	T _r		---	21.6	---	
Turn-Off Delay Time	T _{d(off)}		---	11.2	---	
Fall Time	T _f		---	18.8	---	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	510	---	pF
Output Capacitance	C _{oss}		---	30	---	
Reverse Transfer Capacitance	C _{rss}		---	16	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,4}	I _S	V _G =V _D =0V, Force Current	---	---	2.2	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

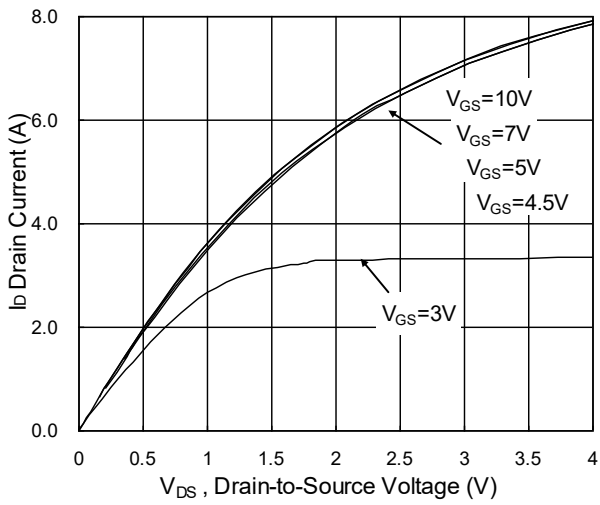


Fig.1 Typical Output Characteristics

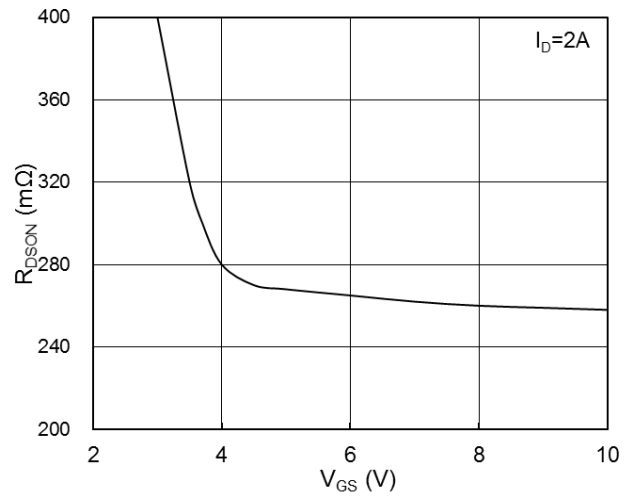


Fig.2 On-Resistance vs. G-S Voltage

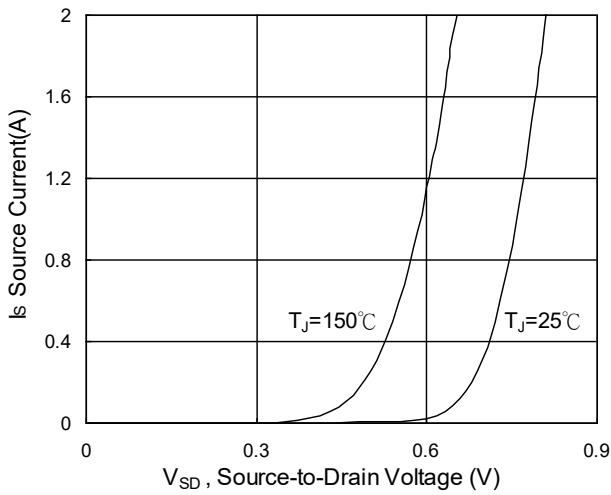


Fig.3 Source Drain Forward Characteristics

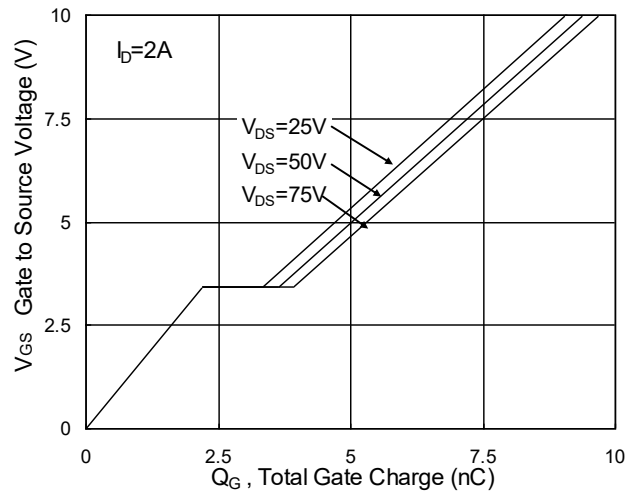


Fig.4 Gate-Charge Characteristics

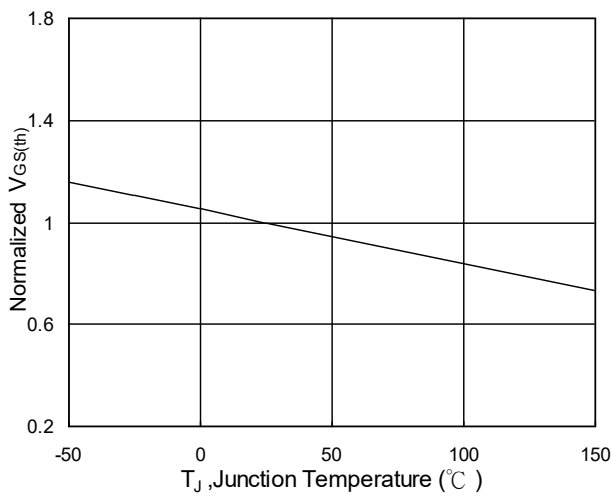


Fig.5 Normalized VGS(th) vs. TJ

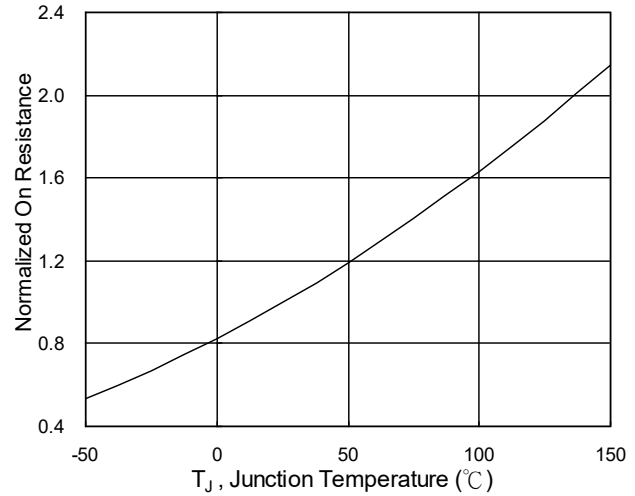


Fig.6 Normalized RDS(on) vs. TJ

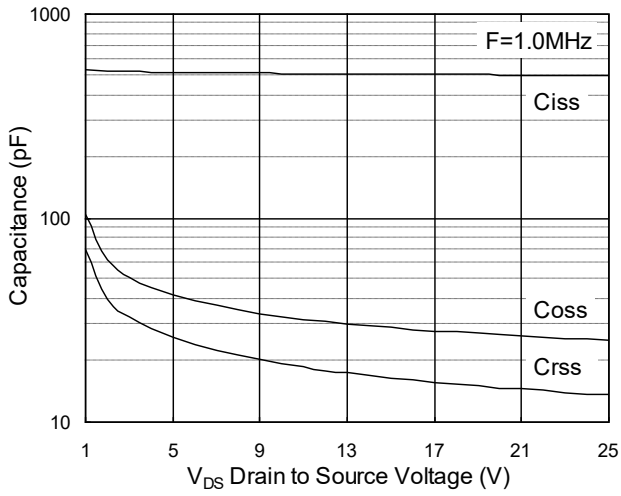


Fig.7 Capacitance

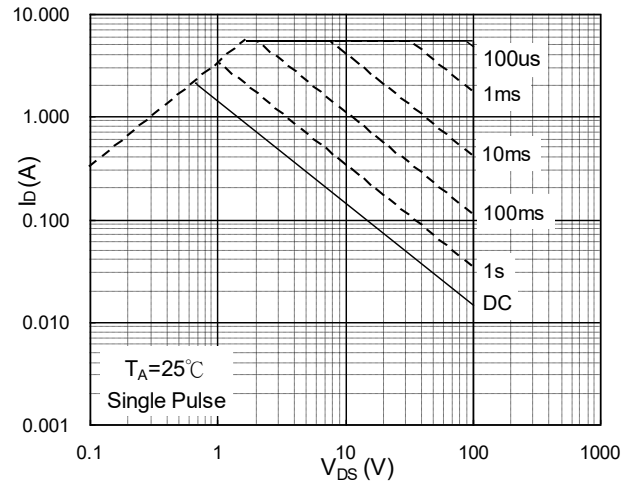


Fig.8 Safe Operating Area

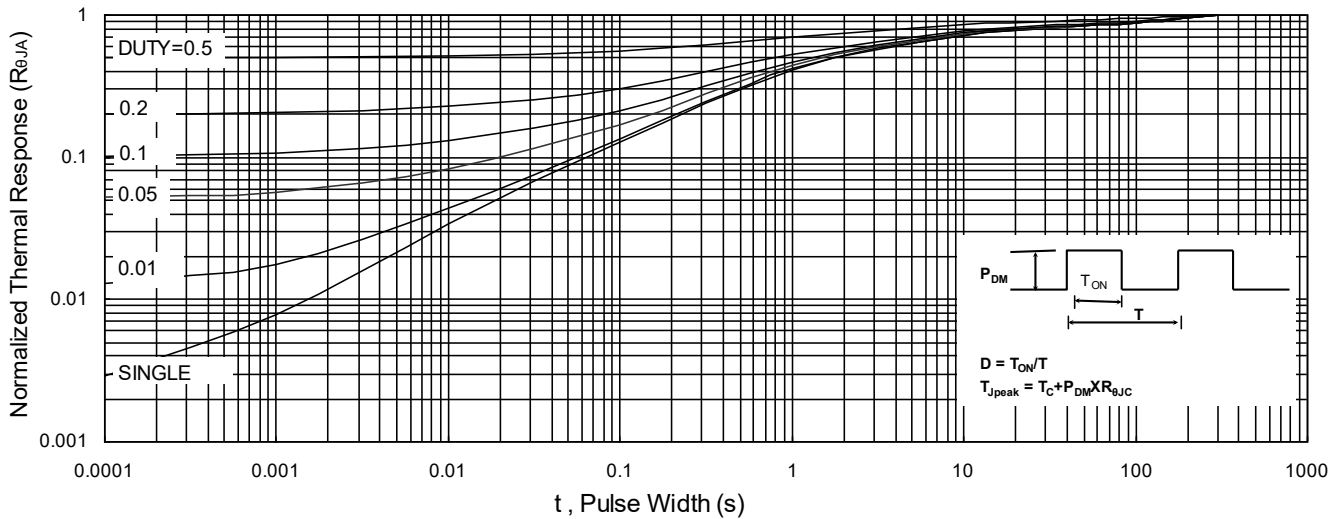


Fig.9 Normalized Maximum Transient Thermal Impedance

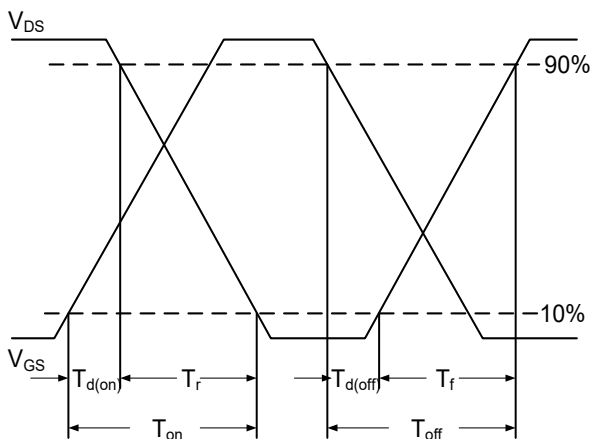


Fig.10 Switching Time Waveform

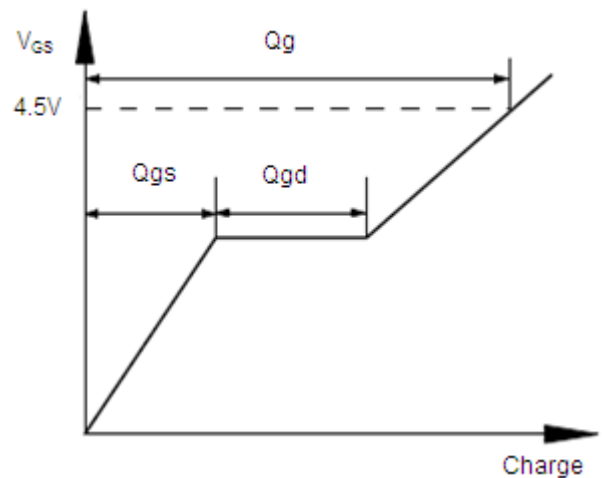
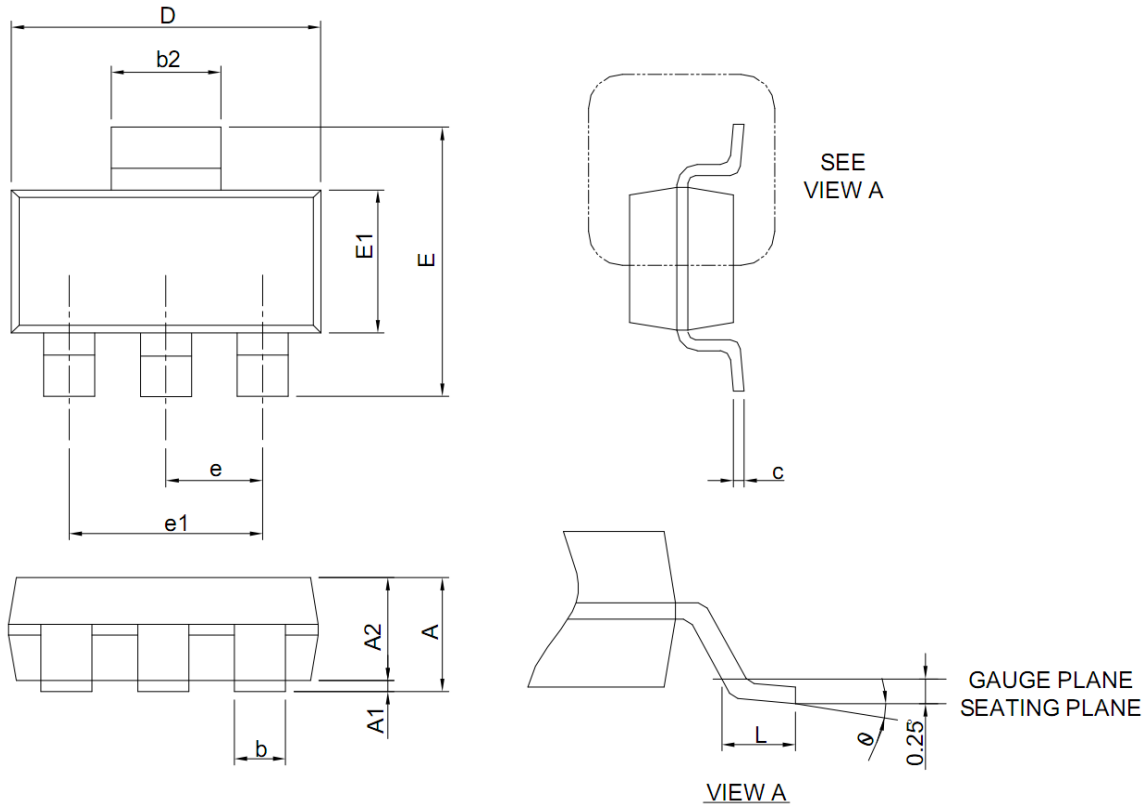


Fig.11 Gate Charge Waveform

SOT223 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	1.50	1.65	1.80	A1	0.02	0.06	0.10
A2	1.50	1.60	1.70	b	0.66	0.72	0.80
b2	2.90	3.00	3.10	c	0.23	0.30	0.35
D	6.30	6.50	6.70	E	6.70	7.00	7.30
E1	3.30	3.50	3.70	e	2.30 REF		
e1	4.60 REF			L	0.75	--	1.15
θ	0°	--	10°				